Abstracts

Temperature and Dispersion Effect Extentions of Chalmers Nonlinear HEMT and MESFET Model

I. Angelov, L. Bengtsson and M. Garcia. "Temperature and Dispersion Effect Extentions of Chalmers Nonlinear HEMT and MESFET Model." 1995 MTT-S International Microwave Symposium Digest 95.3 (1995 Vol. III [MWSYM]): 1515-1518.

Temperature and dispersion effects have been investigated and included in the Chalmers nonlinear model for HEMTs and MESFETS. DC, pulsed DC, low frequency (10Hz-10MHz), RF and small signal S-parameter measurements (1 -18GHz) have been made on a large number of HEMT and MESFET devices from different manufacturers in the temperature range 17-400K in order to evaluate the model.

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